



Cite this: *J. Mater. Chem. C*, 2020, **8**, 5293

DOI: 10.1039/d0tc90064h

rsc.li/materials-c

Correction: High-performance optoelectronic memory based on bilayer MoS₂ grown by Au catalyst

Fengyou Yang,^{ab} Shengyao Chen,^{ac} Huimin Feng,^{ab} Cong Wang,^d Xiaofeng Wang,^{ab} Shu Wang,^{ab} Zhican Zhou,^{ac} Bo Li,^{ab} Lijun Ma,^a Haiguang Yang,^{ab} Yong Xie^e and Qian Liu^{*abc}

Correction for 'High-performance optoelectronic memory based on bilayer MoS₂ grown by Au catalyst' by Fengyou Yang *et al.*, *J. Mater. Chem. C*, 2020, **8**, 2664–2668.

The author regret an error in Fig. 4d of the published article; the corrected version of Fig. 4d is shown here. The rest of Fig. 4 and the caption are unchanged.

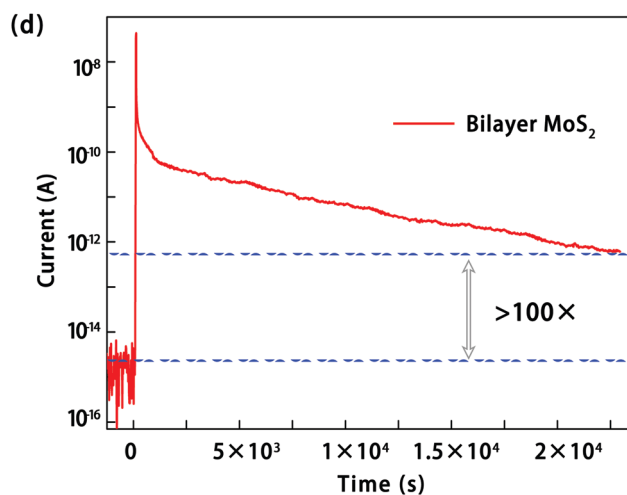


Fig. 4 (d) The retention time property of the bilayer MoS₂ optoelectronic memory.

Please note that these changes do not affect the results and conclusions reported in the article.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a CAS Key Laboratory of Nanosystem and Hierarchical Fabrication, CAS Center for Excellence in Nanoscience, National Center for Nanoscience and Technology, Beijing 100190, P. R. China. E-mail: liuq@nanoctr.cn

^b University of Chinese Academy of Sciences, Beijing 100049, P. R. China

^c MOE Key Laboratory of Weak-Light Nonlinear Photonics, TEDA Applied Physics Institute, School of Physics, Nankai University, Tianjin 300457, China

^d Division of Physics and Applied Physics, School of Physical and Mathematical Sciences, Nanyang Technological University, Singapore 637371, Singapore

^e Department of Physics, Beihang University, Beijing 100083, China

